

P-Channel JFET Switch



J174 – J177 / SST174 – SST177

FEATURES

- Low Insertion Loss
- No Offset or Error Generated By Closed Switch
 - Purely Resistive
 - High Isolation Resistance From Driver
- Short Sample and Hold Aperture Time
- Fast Switching

APPLICATIONS

- Analog Switches
- Choppers
- Commutators

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise specified)

Gate-Drain or Gate-Source Voltage	30V
Gate Current	50mA
Storage Temperature Range	-55°C to +150°C
Operating Temperature Range	-55°C to +135°C
Lead Temperature (Soldering, 10sec)	300°C
Power Dissipation	350mW
Derate above 25°C	3.3mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

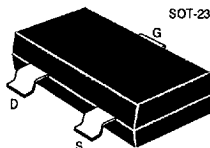
Part	Package	Temperature Range
J174-J177	Plastic TO-92	-55°C to +135°C
SST174-SST177	Plastic SOT-23	-55°C to +135°C

For Sorted Chips in Carriers see 2N5114 series.

PIN CONFIGURATION



TO-92



SOT-23

5508

PRODUCT MARKING (SOT-23)	
SST174	P04
SST175	P05
SST176	P06
SST177	P07

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	174			175			176			177			UNITS	TEST CONDITIONS				
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX						
I _{GSS}	Gate Reverse Current (Note 1)			1			1			1			1	nA	V _{DS} = 0, V _{GS} = 20V				
V _{GS(off)}	Gate Source Cutoff Voltage	5		10	3		6	1		4	0.8		2 25	V	V _{DS} = -15V, I _D = -10nA				
BV _{GSS}	Gate Source Breakdown Voltage	30			30			30			30				V _{DS} = 0, I _G = 1μA				
I _{DSS}	Drain Saturation Current (Note 2)	-20		-135	-7		-70	-2		-35	-1.5		-20	mA	V _{DS} = -15V, V _{GS} = 0				
I _{D(off)}	Drain Cutoff Current (Note 1)			-1			-1			-1			-1	nA	V _{DS} = -15V, V _{GS} = 10V				
r _{DS(on)}	Drain-Source ON Resistance			85			125			250			300	Ω	V _{GS} = 0, V _{DS} = -0.1V				
C _{dg(off)}	Drain-Gate OFF Capacitance		5.5			5.5			5.5			5.5		pF	V _{DS} = 0, V _{GS} = 10V		f = 1MHz (Note 3)		
C _{sg(off)}	Source-Gate OFF Capacitance		5.5			5.5			5.5			5.5							
C _{dg(on)} + C _{sg(on)}	Drain-Gate Plus Source Gate ON Capacitance	32			32			32			32				V _{DS} = V _{GS} = 0				
t _{d(on)}	Turn On Delay Time		2			5			15			20		ns	Switching Time Test Conditions (Note 3)				
t _r	Rise Time		5			10			20			25			V _{DD} 174 175 176 177 -10V -6V -6V -6V V _{GS(off)} 12V 8V 3V 3V R _L 560Ω 12kΩ 5.6kΩ 10kΩ V _{GS(on)} 0V 0V 0V 0V				
t _{d(off)}	Turn Off Delay Time		5			10			15			20							
t _f	Fall Time		10			20			20			25							

NOTES: 1. Approximately doubles for every 10°C increase in T_A
 2. Pulse test duration $\sim 300\mu s$; duty cycle $\leq 3\%$.
 3. For design reference only, not 100% tested.

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